

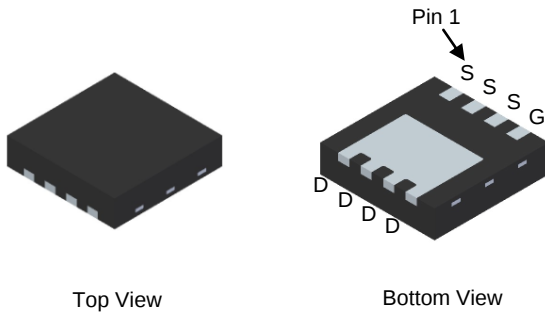
Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D $T_C = +25^\circ C$
100V	8.8m Ω @ $V_{GS} = 10V$	47A
	12.9m Ω @ $V_{GS} = 4.5V$	39A

Description and Applications

This new generation N-Channel Enhancement Mode MOSFET is designed to minimize $R_{DS(ON)}$ and yet maintain superior switching performance. This device is ideal for use in notebook battery power management and loadswitch.

- Backlighting
- Power Management Functions
- DC-DC Converters



Top View

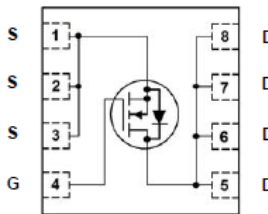
Bottom View

Features and Benefits

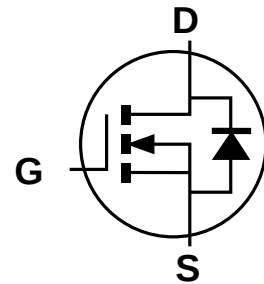
- 100% Unclamped Inductive Switch (UIS) Test in Production
- High Conversion Efficiency
- Low $R_{DS(ON)}$ – Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

- Case: V-DFN3333-8 (Type B)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Below Diagram
- Terminals: Finish –NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 0.03 grams (Approximate)



Top View
Internal Schematic



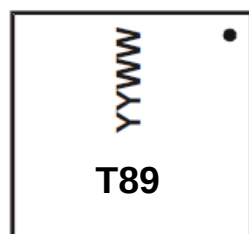
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT10H009LCG-7	V-DFN3333-8 (Type B)	2,000/Tape & Reel
DMT10H009LCG-13	V-DFN3333-8 (Type B)	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



T89 = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 18 = 2018)
WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	100	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 6)	Steady State	T _A = +25°C T _A = +70°C	I _D	12.4 9.9	A
Continuous Drain Current, V _{GS} = 10V	Steady State	T _C = +25°C T _C = +70°C	I _D	47 37	A
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	22	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I _{DM}	160	A
Pulsed Body Diode Continuous Current (10μs Pulse, Duty Cycle = 1%)			I _{SM}	160	A
Avalanche Current, L = 0.3mH (Note 8)			I _{AS}	21	A
Avalanche Energy, L = 0.3mH (Note 8)			E _{AS}	66	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	1	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	129	°C/W
Total Power Dissipation (Note 6)	P _D	2.1	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	59	°C/W
Thermal Resistance, Junction to Case	R _{θJC}	4.2	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	100	—	—	V	V _{GS} = 0V, I _D = 1mA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 80V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1.1	—	2.5	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	7.2	8.8	mΩ	V _{GS} = 10V, I _D = 20A
		—	9.8	12.9	mΩ	V _{GS} = 4.5V, I _D = 5A
Diode Forward Voltage	V _{SD}	—	0.8	1.2	V	V _{GS} = 0V, I _S = 20A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{ISS}	—	2309	—	pF	V _{DS} = 50V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{OSS}	—	536	—		
Reverse Transfer Capacitance	C _{ISS}	—	13.7	—		
Gate Resistance	R _G	—	1.9	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	—	20.2	—	nC	V _{DD} = 50V, I _D = 20A, V _{GS} = 4.5V
Gate-Source Charge	Q _{gs}	—	7.0	—		
Gate-Drain Charge	Q _{gd}	—	8.5	—		
Turn-On Delay Time	t _{D(ON)}	—	5.4	—	ns	V _{DD} = 50V, V _{GS} = 10V, I _D = 20A, R _G = 3Ω
Turn-On Rise Time	t _R	—	10.6	—		
Turn-Off Delay Time	t _{D(OFF)}	—	28.3	—		
Turn-Off Fall Time	t _F	—	14.9	—		
Reverse Recovery Time	t _{RR}	—	44.3	—	ns	I _F = 20A, di/dt = 100A/μs
Reverse Recovery Charge	Q _{RR}	—	65.5	—	nC	

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

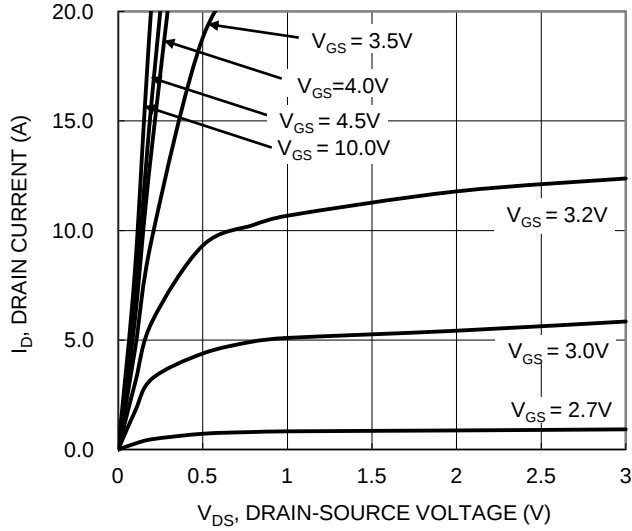


Figure 1. Typical Output Characteristic

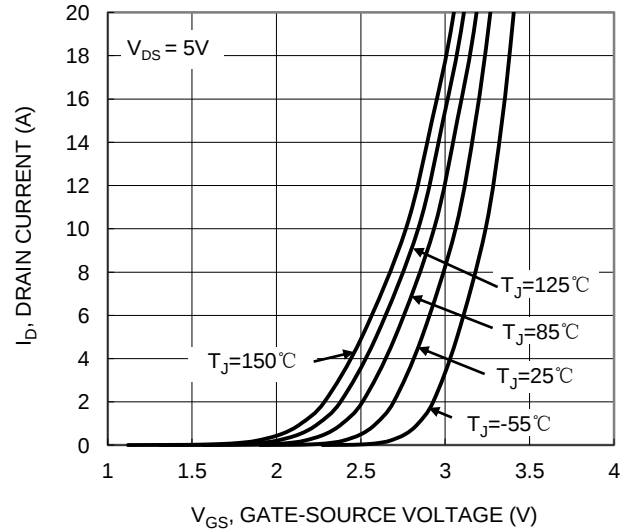


Figure 2. Typical Transfer Characteristic

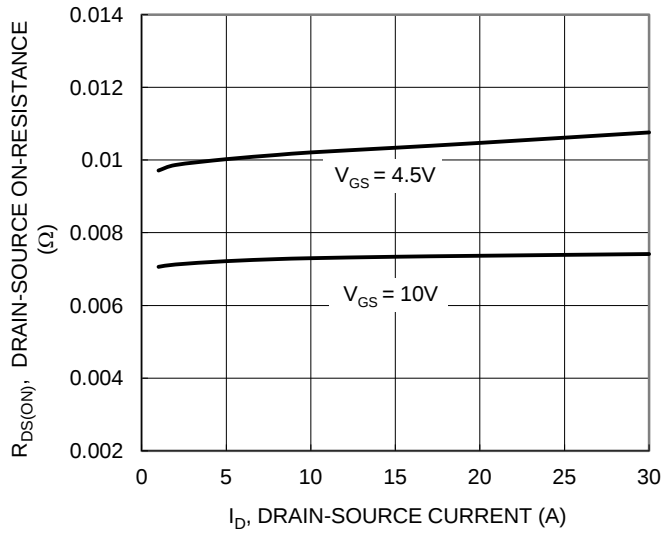


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

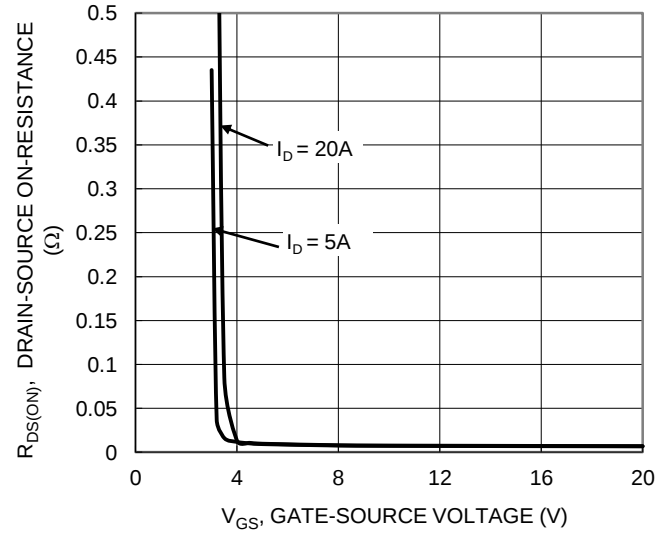


Figure 4. Typical Transfer Characteristic

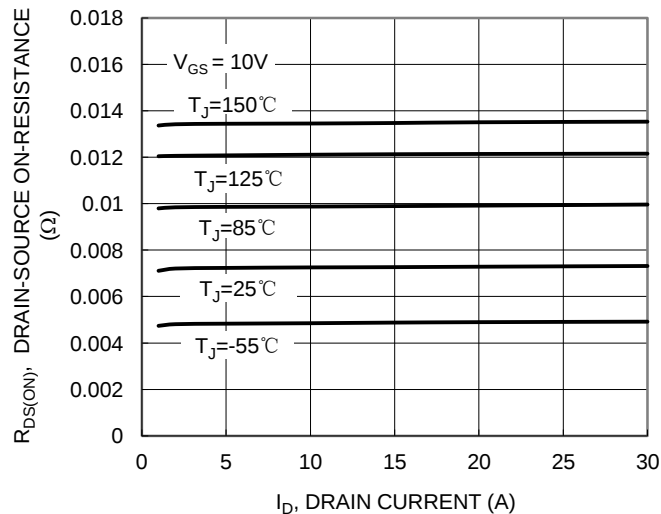


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

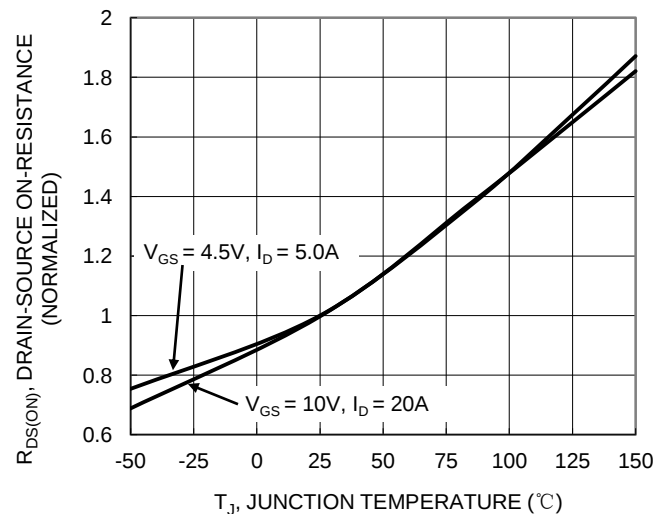
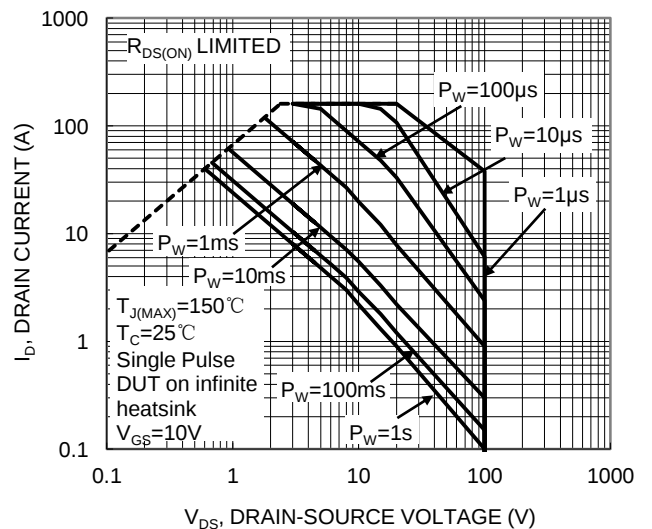
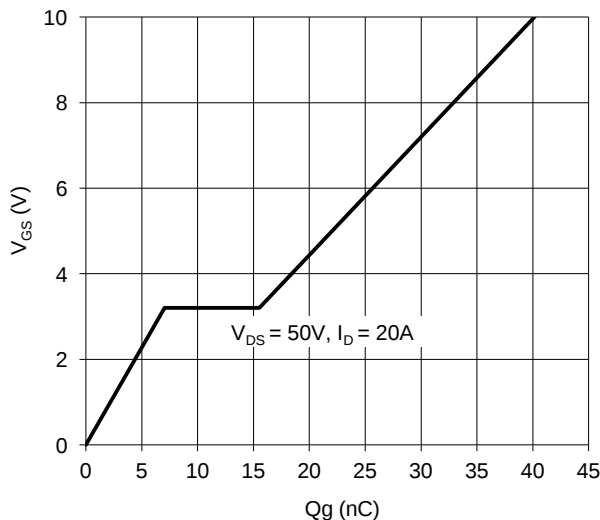
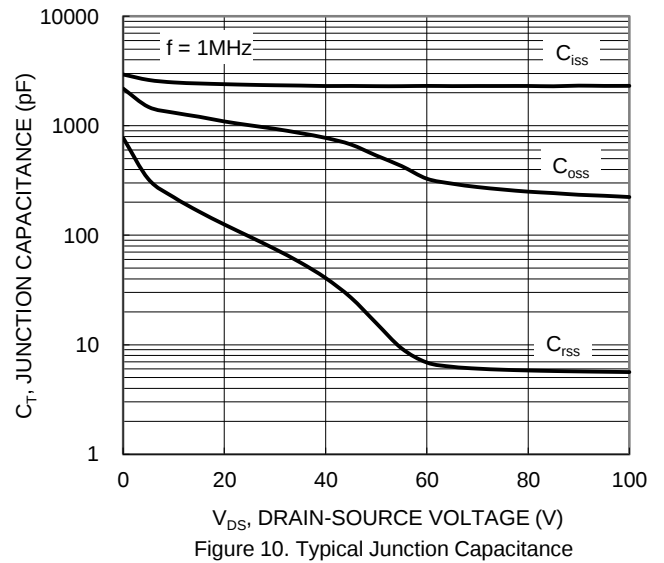
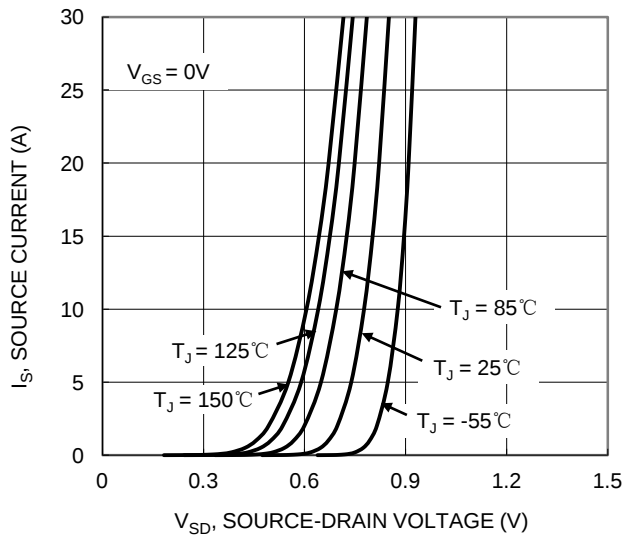
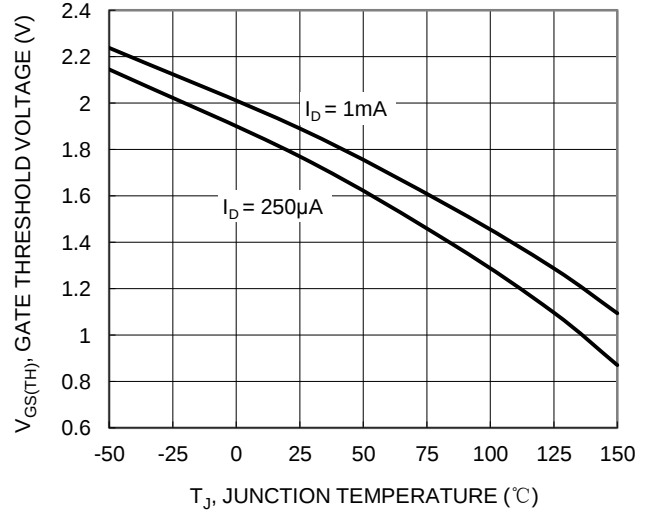
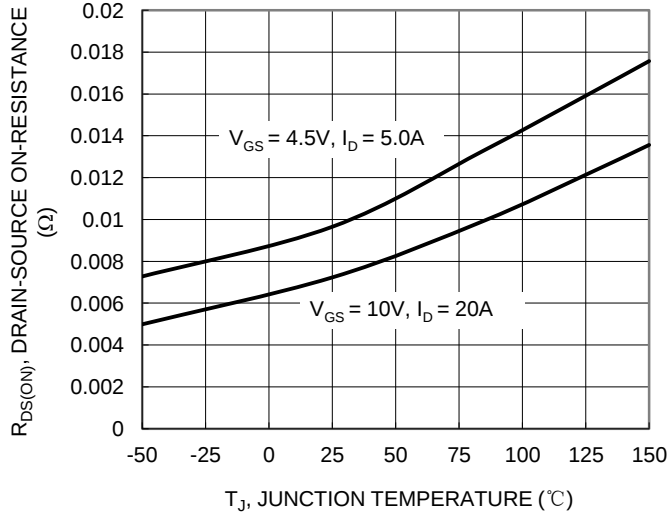


Figure 6. On-Resistance Variation with Junction Temperature



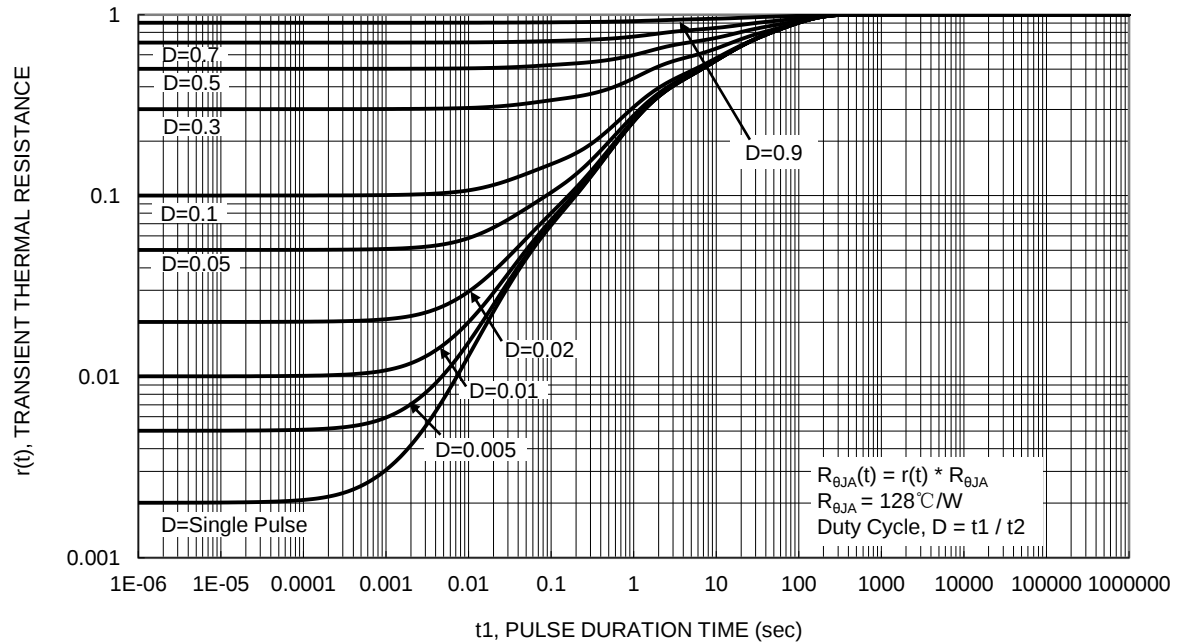
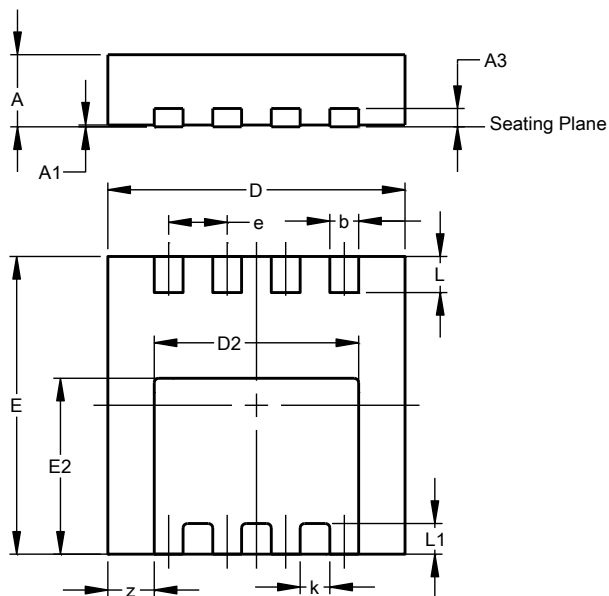


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

V-DFN3333-8 (Type B)

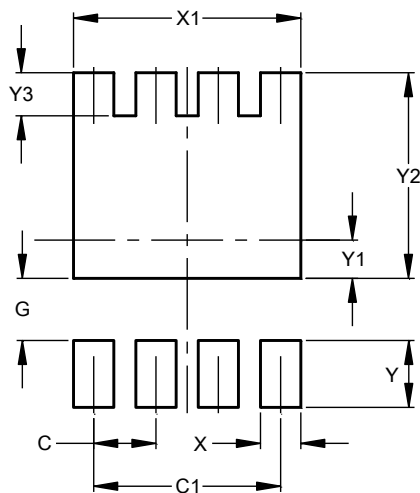


V-DFN3333-8 (Type B)			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	--	--	0.203
b	0.27	0.37	0.32
D	3.25	3.35	3.30
D2	2.17	2.37	2.27
E	3.25	3.35	3.30
E2	1.85	2.05	1.95
e	--	--	0.65
k	--	--	0.33
L	0.35	0.45	0.40
L1	--	--	0.34
z	--	--	0.515
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

V-DFN3333-8 (Type B)



Dimensions	Value (in mm)
C	0.650
C1	1.950
G	0.650
X	0.420
X1	2.370
Y	0.700
Y1	0.400
Y2	2.150
Y3	0.450

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